

Amendments to the Claims

The following listing of the claims replaces all previous amendments and listings of the claims.

1. (Previously Presented) A wet treatment method useful in at least one of a chemical processing step and a rinsing step performed upon fabrication of semiconductor devices, which comprises a sub-step in which:

a substrate under treatment is treated with a desired liquid while causing said substrate to revolve around an axis of rotation outside said substrate such that said desired liquid flowing on a surface of said substrate is maintained flowing under a centrifugal force greater than gravitation, the surface of the substrate disposed on a horizontal plane perpendicular to the axis of rotation, and

said substrate is treated while supplying an additional amount of said desired liquid at a flow rate at least equal to a discharge rate of said desired liquid, the additional amount of the desired liquid provided to the substrate only in a direction perpendicular to the axis of rotation, while

directly spraying with the desired liquid only a top cover of a chamber in which the desired liquid is supplied to the substrate,

whereby said substrate is evenly treated at said surface thereof with said desired liquid while avoiding development of such a situation that flows of said desired liquid run against each other on said surface of said substrate or a flow of said desired liquid stagnates on said surface of said substrate.

2. (Previously Presented) The wet treatment method according to claim 1, wherein said desired liquid has a high viscosity, a high adhesion, or contains an organic substance.

3. (Previously Presented) The wet treatment method according to claim 1, wherein said sub-step is conducted before a final treatment in at least one of said chemical processing step and said rinsing step.

4. (Currently Amended) The wet treatment method according to claim 3, wherein said wet treatment method is used in said rinsing step such that the desired liquid is used to rinse a chemical employed in said chemical processing step; and said chemical employed in the chemical processing step has a high viscosity, high adhesion, contains an organic substance, [[,]] or has an etching rate that increases when mixed with water.

5. (Previously Presented) The wet treatment method according to claim 2, wherein said wet treatment method is used in said rinsing step such that the desired liquid is used to rinse a chemical employed in said chemical processing step; and said chemical is used in the chemical processing step comprises a solution of at least one of amines and ammonium fluoride dissolved as an effective component in an organic solvent or a water-containing organic solvent.

6. (Previously Presented) A wet treatment method according to claim 1, wherein said desired liquid comprises pure water.

7.-11. (Canceled)

12. (Currently Amended) A method of treating a substrate, comprising:
rotating the substrate about an axis disposed apart from the substrate, a surface of the substrate disposed on a horizontal plane perpendicular to the axis;
supplying a liquid to treat the surface of the substrate in a direction only perpendicular to the axis; and
directly spraying with the liquid only a top cover of a chamber in which the liquid is supplied to the substrate,

whereby said substrate is evenly treated at said surface thereof with said ~~desired~~ liquid while avoiding development of such a situation that flows of said ~~desired~~ liquid run against each other on said surface of said substrate or a flow of said ~~desired~~ liquid stagnates on said surface of said substrate.

13. (Previously Presented) The method according to claim 12, wherein the substrate is rotated such that a centrifugal force is greater than a gravitational force.

14. (Previously Presented) The method according to claim 12, wherein supplying comprises supplying the liquid at a rate at least equal to a rate of removal of the liquid from the substrate due to a centrifugal force.

15. (Previously Presented) The method according to claim 12, wherein rotating comprises rotating the substrate such that the supplied liquid flows in a direction of liquid flow from the substrate due to a centrifugal force.

16. (Previously Presented) The method according to claim 15, wherein the liquid comprises water.

17. (Previously Presented) The method according to claim 16, wherein the liquid comprises chemical etchant.

18. (Previously Presented) The wet treatment method according to claim 1, wherein a nozzle sprays the top cover of the chamber, the nozzle disposed on a rotating table on which the substrate is disposed.

19. (Previously Presented) The wet treatment method according to claim 1, wherein directly spraying comprises directly spraying the desired liquid from a nozzle, the nozzle configured to directly spray only the top cover of the chamber.

20. (Previously Presented) The wet treatment method according to claim 19, wherein the nozzle is disposed on a table on which the substrate is disposed.

21. (Previously Presented) The wet treatment method according to claim 1, wherein a plurality of nozzles configured to clean the top cover with the desired liquid spray the top cover of the chamber.

22. (Previously Presented) The method according to claim 12, wherein a nozzle sprays the top cover of the chamber, the nozzle disposed on a rotating table on which the substrate is disposed.

23. (Previously Presented) The method according to claim 12, wherein directly spraying comprises directly spraying the liquid from a nozzle, the nozzle configured to directly spray only the top cover of the chamber

24. (Previously Presented) The method according to claim 23, wherein the nozzle is disposed on a table on which the substrate is disposed

25. (Previously Presented) The method according to claim 12, wherein a plurality of nozzles configured to clean the top cover with the liquid spray the top cover of the chamber.